

*Phase leg
Serie & SiC parallel diodes
Super Junction
MOSFET Power Module*

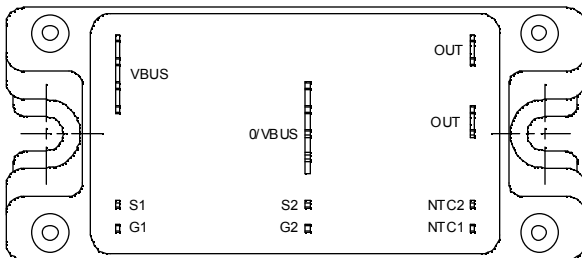
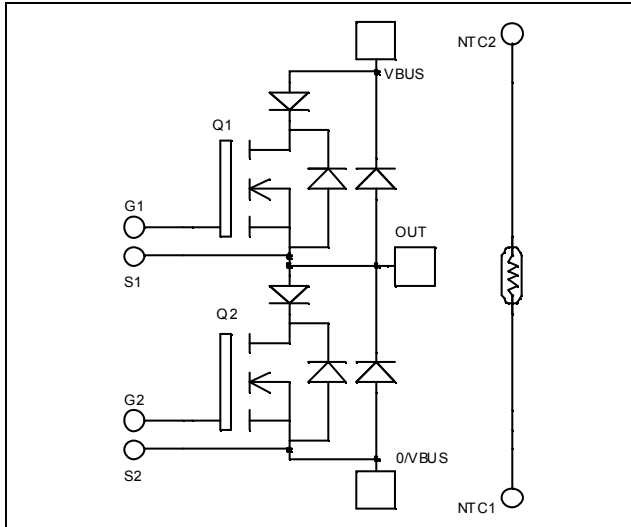
$V_{DSS} = 800V$
 $R_{DSon} = 150m\Omega$ max @ $T_j = 25^\circ C$
 $I_D = 28A$ @ $T_c = 25^\circ C$

Application

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- **COOLMOS** Power Semiconductors
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
- **Parallel SiC Schottky Diode**
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature Independent switching behavior
 - Positive temperature coefficient on VF
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	800	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	28
		$T_c = 80^\circ C$	21
I_{DM}	Pulsed Drain current	112	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	150	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	277
I_{AR}	Avalanche current (repetitive and non repetitive)	17	A
E_{AR}	Repetitive Avalanche Energy	0.5	mJ
E_{AS}	Single Pulse Avalanche Energy	670	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 800\text{V}$	$T_j = 25^\circ\text{C}$			50	μA
		$V_{GS} = 0\text{V}, V_{DS} = 800\text{V}$	$T_j = 125^\circ\text{C}$			375	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 14\text{A}$				150	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2\text{mA}$		2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$				± 150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$		4507		pF
C_{oss}	Output Capacitance	$V_{DS} = 25\text{V}$		2092		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		108		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 400\text{V}$ $I_D = 28\text{A}$		180		nC
Q_{gs}	Gate – Source Charge			22		
Q_{gd}	Gate – Drain Charge			90		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @125°C		10		ns
T_r	Rise Time	$V_{GS} = 15\text{V}$		13		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 533\text{V}$		83		
T_f	Fall Time	$I_D = 28\text{A}$ $R_G = 2.5\Omega$		35		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C		291		μJ
E_{off}	Turn-off Switching Energy	$V_{GS} = 15\text{V}, V_{Bus} = 533\text{V}$ $I_D = 28\text{A}, R_G = 2.5\Omega$		278		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C		510		μJ
E_{off}	Turn-off Switching Energy	$V_{GS} = 15\text{V}, V_{Bus} = 533\text{V}$ $I_D = 28\text{A}, R_G = 2.5\Omega$		342		

Series diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 200\text{V}$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 125^\circ\text{C}$		500	
I_F	DC Forward Current			30		A
V_F	Diode Forward Voltage	$I_F = 30\text{A}$		1.1	1.15	V
		$I_F = 60\text{A}$		1.4		
		$I_F = 30\text{A}$	$T_j = 125^\circ\text{C}$	0.9		
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}$ $V_R = 133\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	24		ns
			$T_j = 125^\circ\text{C}$	48		
Q_{rr}	Reverse Recovery Charge	$I_F = 30\text{A}$ $V_R = 133\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	33		nC
			$T_j = 125^\circ\text{C}$	150		

Parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V		150 300	600 3000	μA
I _F	DC Forward Current	T _c = 125°C		15		A
V _F	Diode Forward Voltage	I _F = 15 A		1.6 2.6	1.8 3.0	V
Q _C	Total Capacitive Charge	I _F = 15 A, V _R = 600 V di/dt = 1000 A/μs		42		nC
Q	Total Capacitance	f = 1 MHz, V _R = 200 V		135		pF
		f = 1 MHz, V _R = 400 V		99		

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance	Transistor		0.45	°C/W	
		Series diode		1.2		
		Parallel diode		1.0		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1 mA, 50/60 Hz	2500			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To Heatsink	M5	2.5	4.7	N.m
Wt	Package Weight				160	g

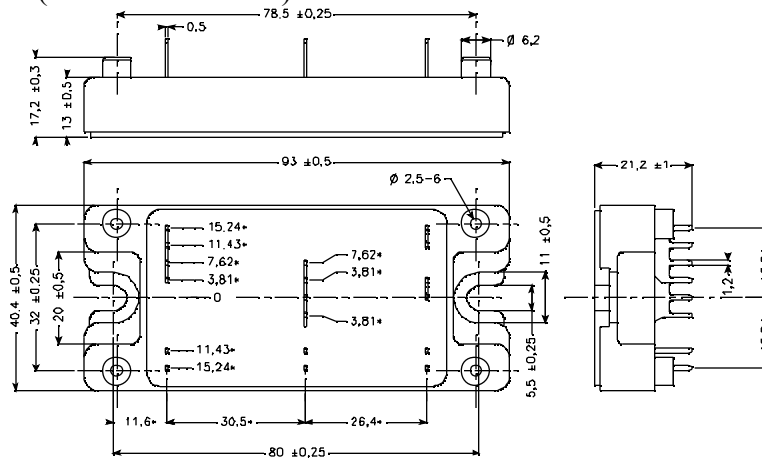
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T} - \frac{1}{T_{25}} \right) \right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

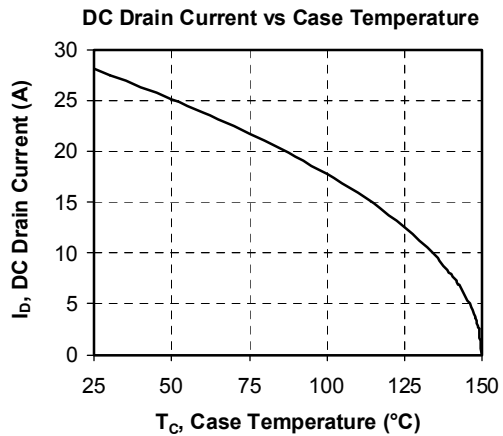
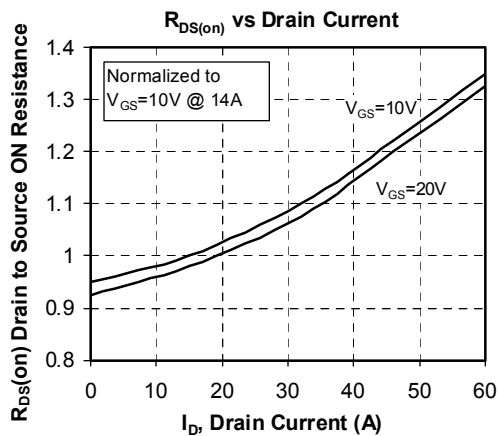
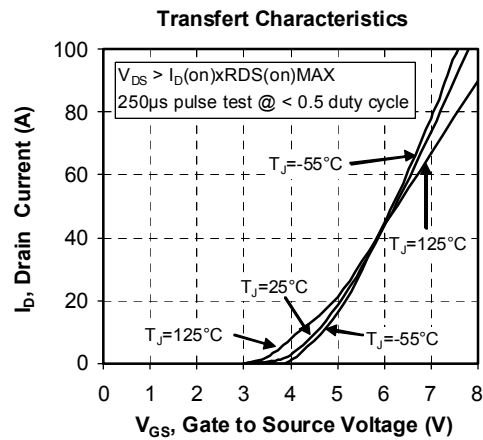
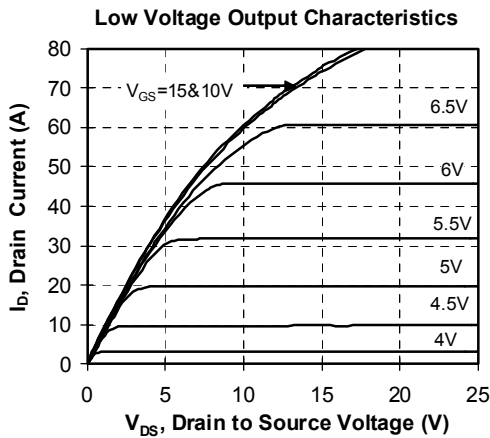
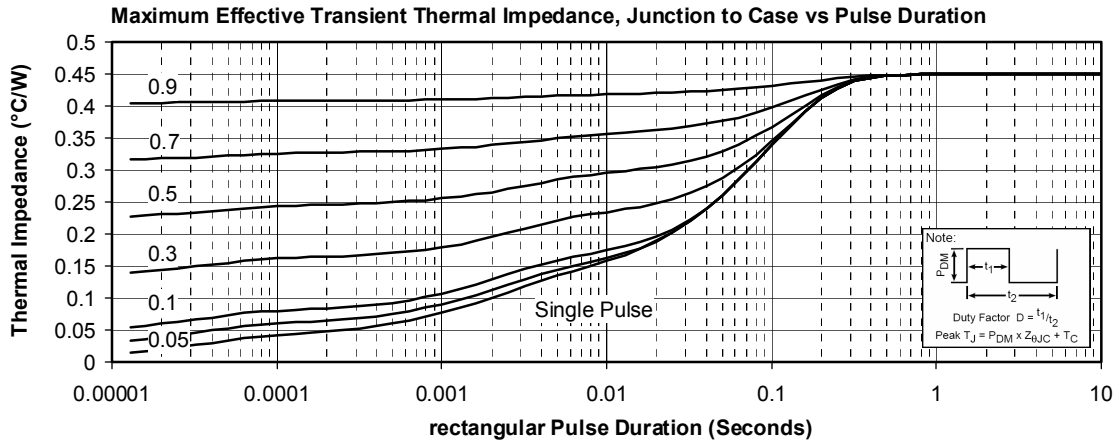
SP4 Package outline (dimensions in mm)

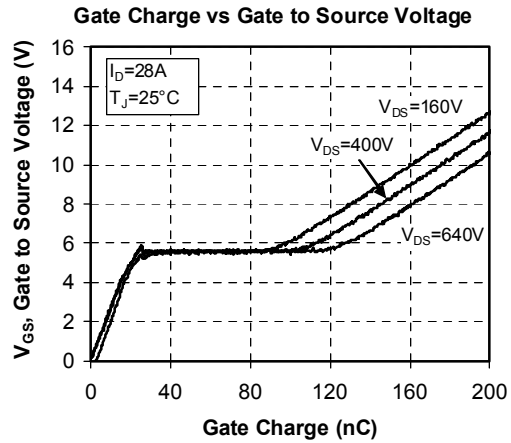
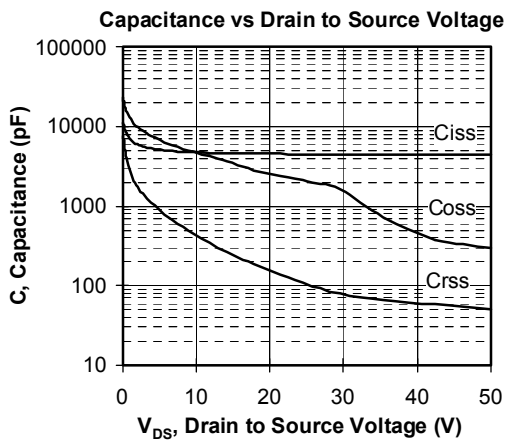
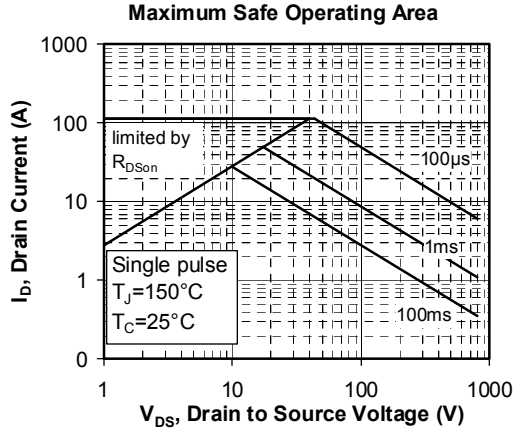
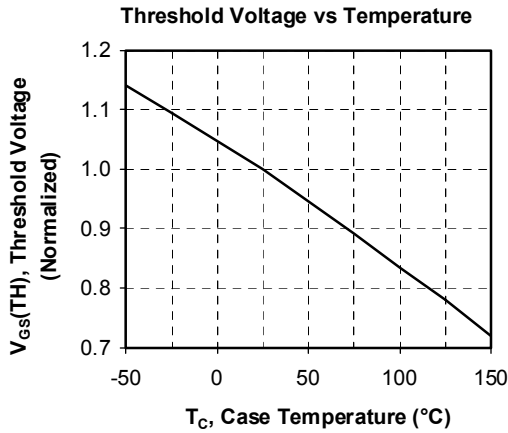
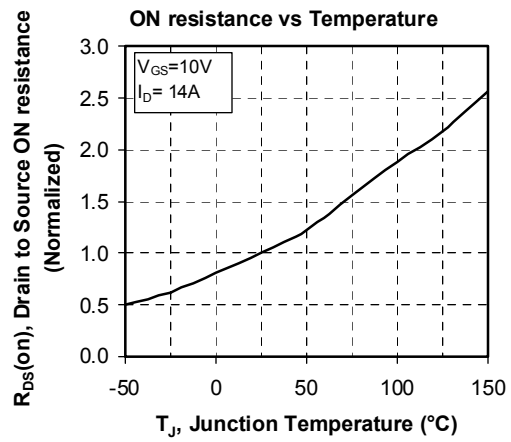
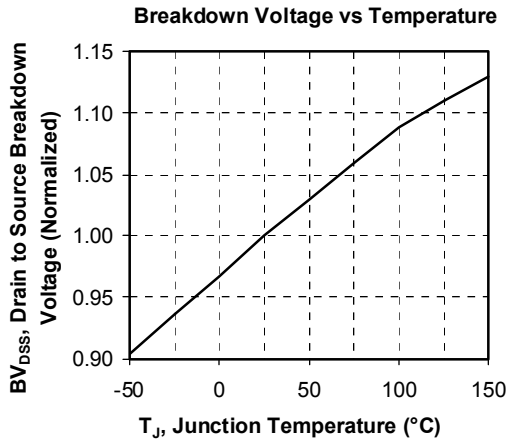


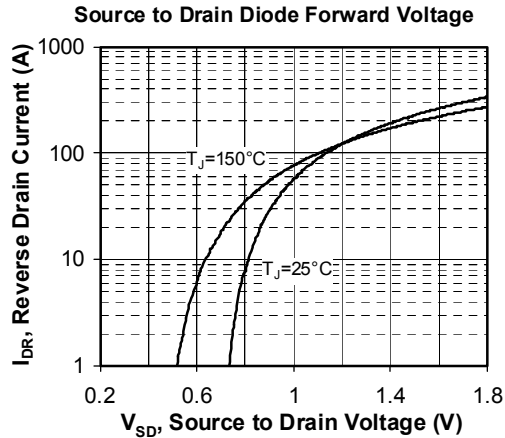
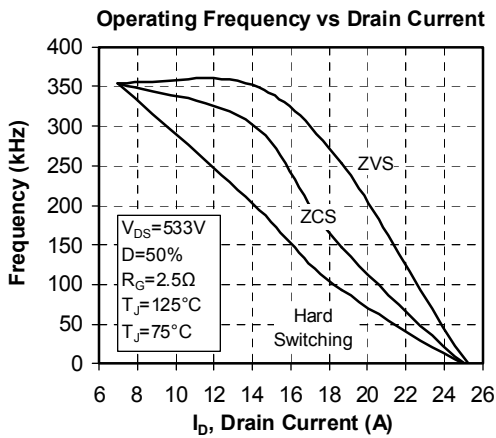
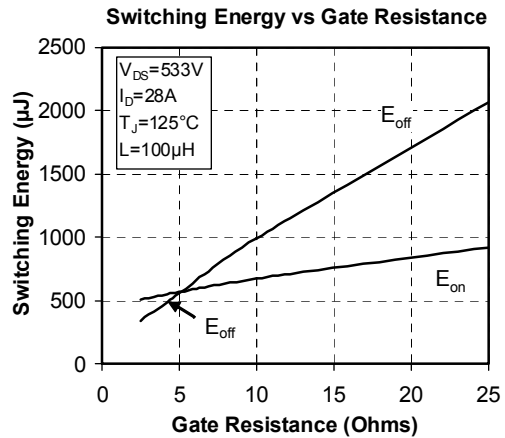
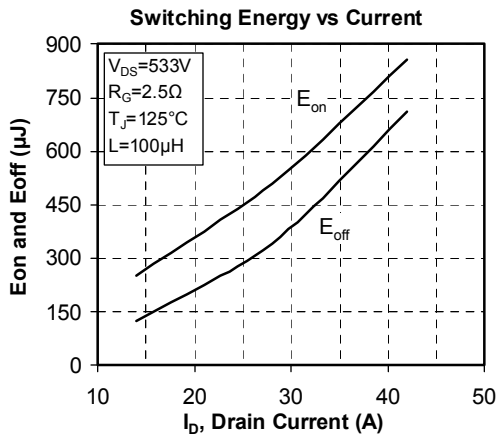
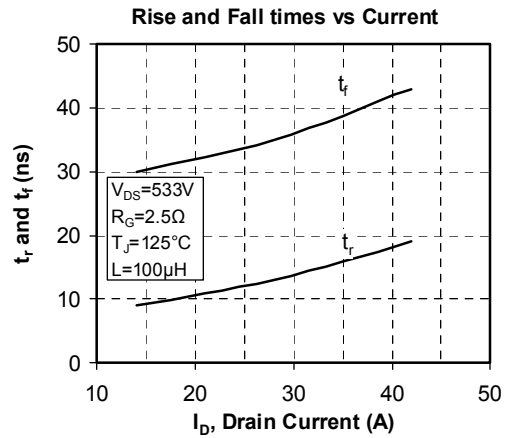
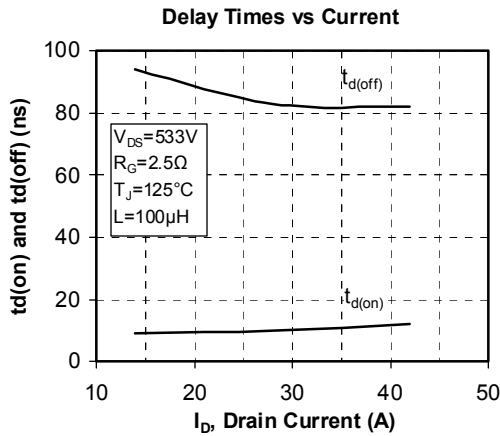
ALL DIMENSIONS MARKED "*" ARE TOLERANCED AS: ± 0.1

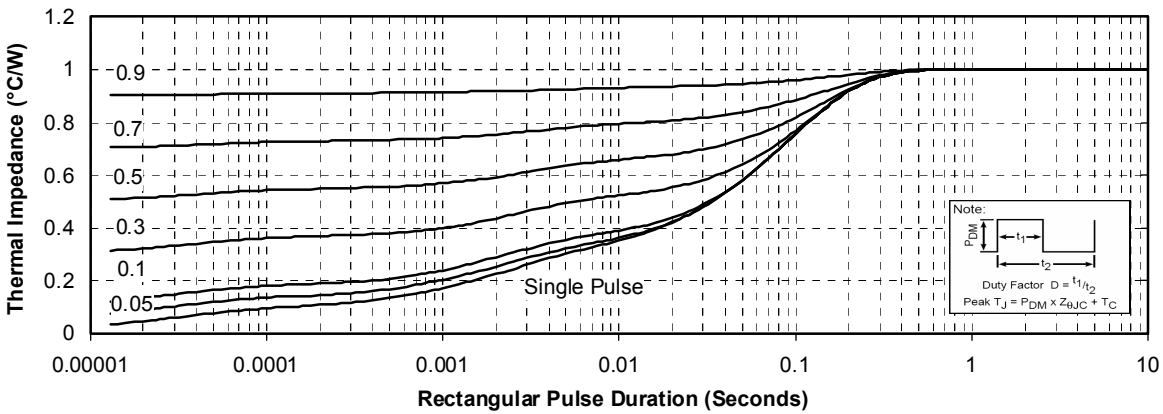
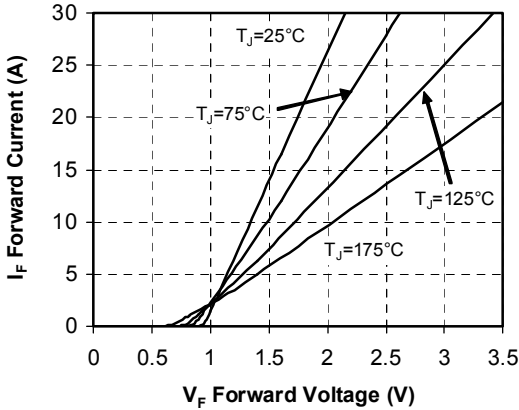
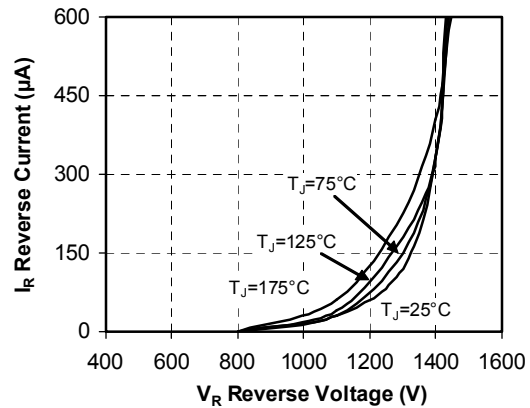
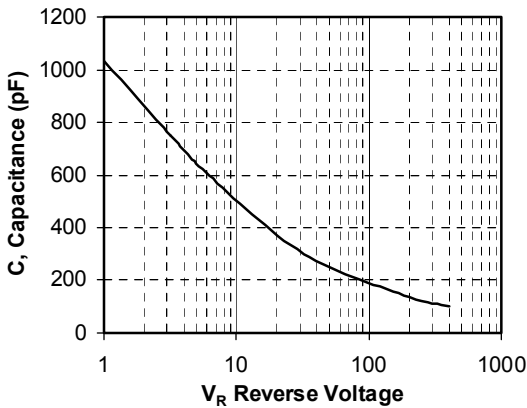
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical CoolMOS Performance Curve







Typical SiC Diode Performance Curve
Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration

Forward Characteristics

Reverse Characteristics

Capacitance vs. Reverse Voltage


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Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.